

2SK1036

Silicon N-channel Power F-MOS FET

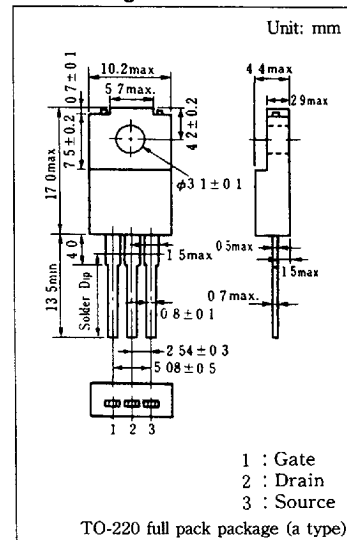
■ Features

- Low ON resistance $R_{DS(on)}$: $R_{DS(on)} = 0.2\Omega$ (typ.)
- High switching rate : $t_r = 80\text{ns}$ (typ.)
- No secondary breakdown

■ Application

- DC-DC converter
- No contact relay
- Solenoid drive
- Motor drive

■ Package Dimensions



■ Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Drain-source voltage	V_{DS}	250	V
Gate-source voltage	V_{GS}	± 20	V
Drain current	DC	I_D	A
	Peak-to-peak value	I_{DP}	
Power dissipation	$T_c = 25^\circ\text{C}$	P_D	W
	$T_a = 25^\circ\text{C}$	2.0	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

■ Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Drain current	I_{DS}	$V_{DS} = 200\text{V}, V_{GS} = 0$			0.1	mA
Gate-source current	I_{GS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$			± 1	μA
Drain-source voltage	V_{DS}	$I_D = 1\text{mA}, V_{GS} = 0$	250			V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	1		5	V
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 5\text{A}$		0.2	0.3	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 5\text{A}$	4.0	6.5		S
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		1500		pF
Output capacitance	C_{oss}			340		pF
Reverse transfer capacitance	C_{rss}			130		pF
Turn-on time	t_{on}	$V_{GS} = 10\text{V}, I_D = 5\text{A}$ $V_{DD} \approx 100\text{V}, R_L = 20\Omega$		60		ns
Fall time	t_f			80		ns
Delay time	$t_d(\text{off})$			240		ns

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